

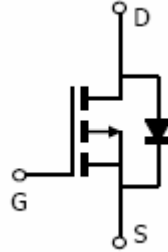
FNK P-Channel Enhancement Mode Power MOSFET

Description

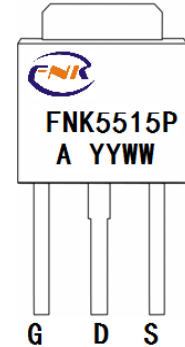
The FNK5515PC uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = -55V, I_D = -15A$
 $R_{DS(ON)} < 80m\Omega @ V_{GS} = -10V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation



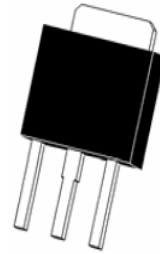
Schematic diagram



Marking and pin assignment

Application

- Power switching application
- Hard switched and high frequency circuits
- DC-DC Converter



TO-252-2L top view



100% UIS TESTED!

100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK5515P	FNK5515PC	TO-251S	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-55	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-15	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	-10	A
Pulsed Drain Current	I_{DM}	-50	A
Maximum Power Dissipation	P_D	50	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

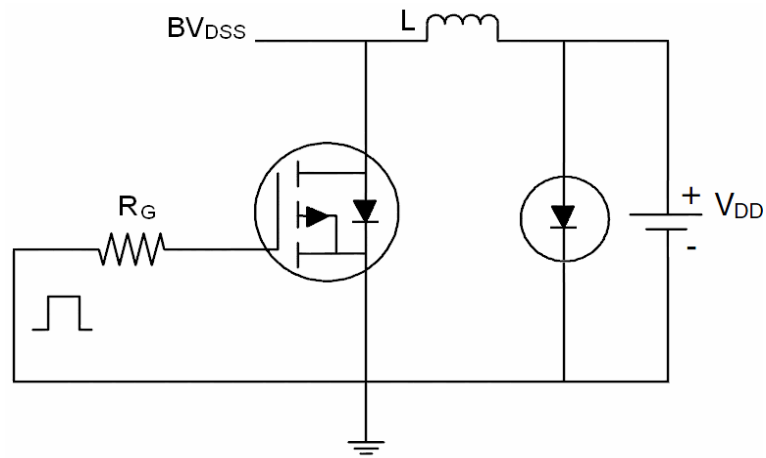
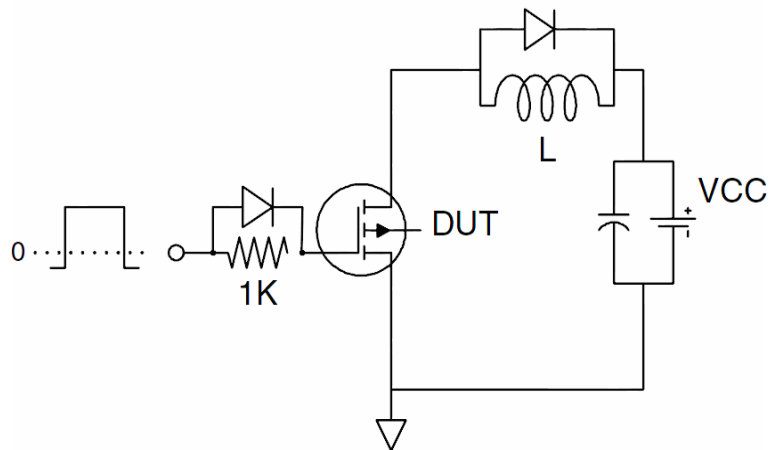
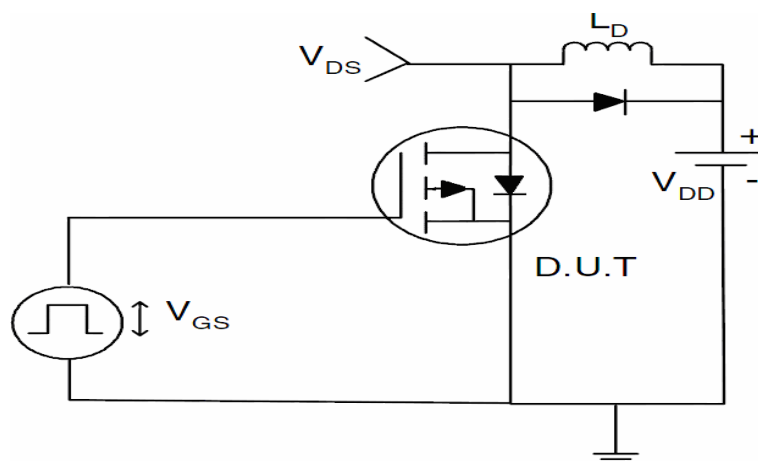
Thermal Resistance ,Junction-to-Case(Note 2)	$R_{\theta JC}$	2.5	$^\circ C/W$
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-55	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-55V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.5	-2.6	-3.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-5A	-	60	80	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-15V, I _D =-5A	16	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0V, F=1.0MHz	-	1450	-	PF
Output Capacitance	C _{oss}		-	145	-	PF
Reverse Transfer Capacitance	C _{rss}		-	110	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =30Ω V _{GS} =-10V, R _{GEN} =6Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	9	-	nS
Turn-Off Delay Time	t _{d(off)}		-	65	-	nS
Turn-Off Fall Time	t _f		-	30	-	nS
Total Gate Charge	Q _g	V _{DS} =-30V, I _D =-5A, V _{GS} =-10V	-	26	-	nC
Gate-Source Charge	Q _{gs}		-	4.5	-	nC
Gate-Drain Charge	Q _{gd}		-	7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-5	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit
1) E_{AS} Test Circuit

2) Gate Charge Test Circuit

3) Switch Time Test Circuit


Typical Electrical and Thermal Characteristics (Curves)

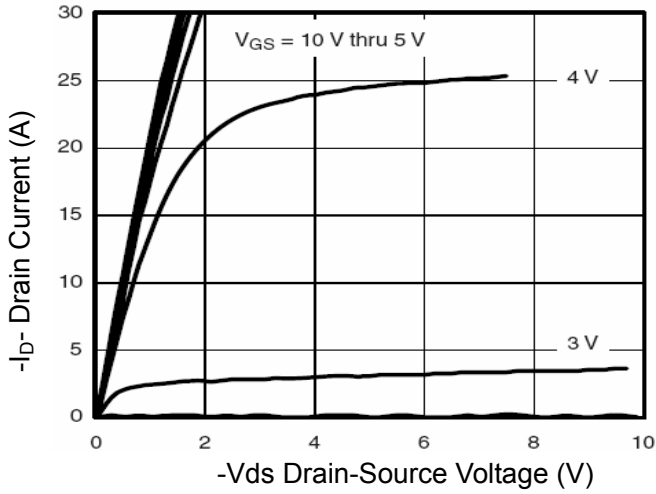


Figure 1 Output Characteristics

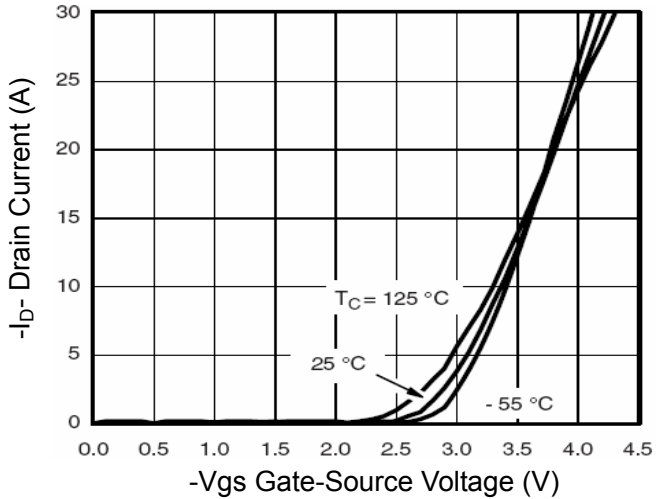


Figure 2 Transfer Characteristics

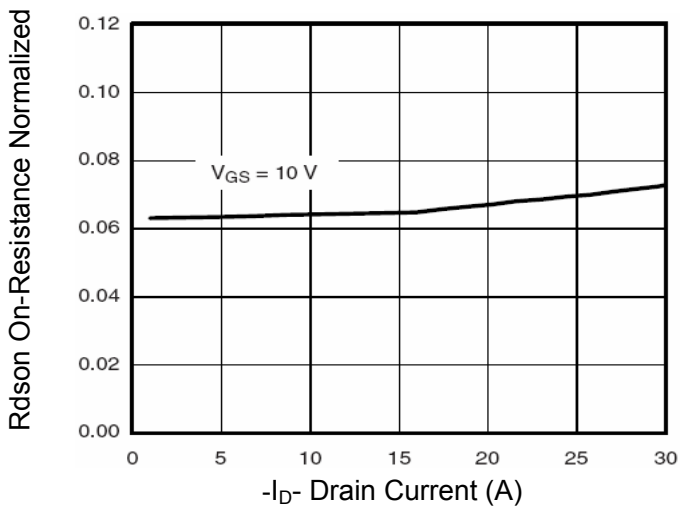


Figure 3 Rdson- Drain Current

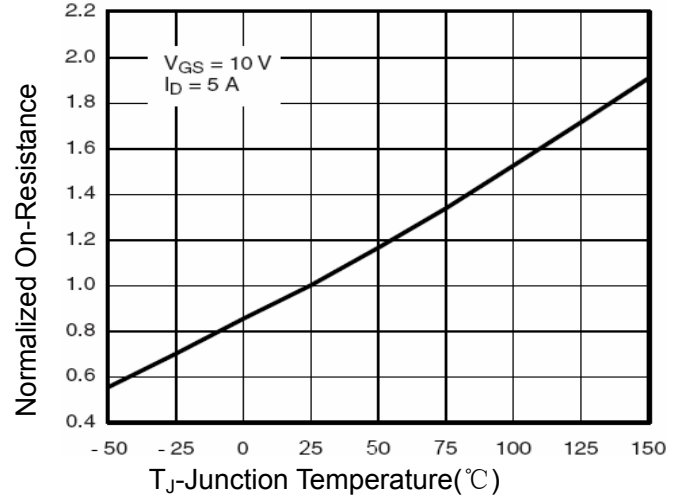


Figure 4 Rdson-Junction Temperature

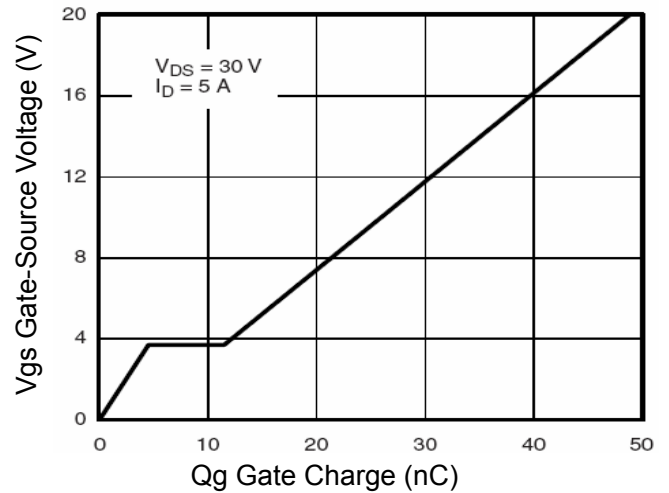


Figure 5 Gate Charge

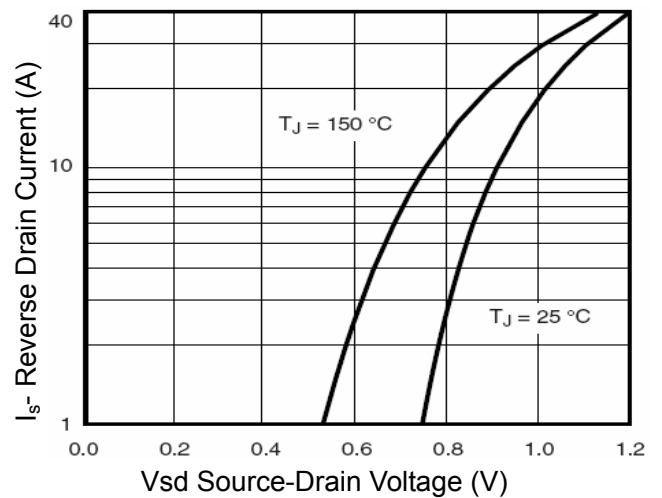


Figure 6 Source- Drain Diode Forward

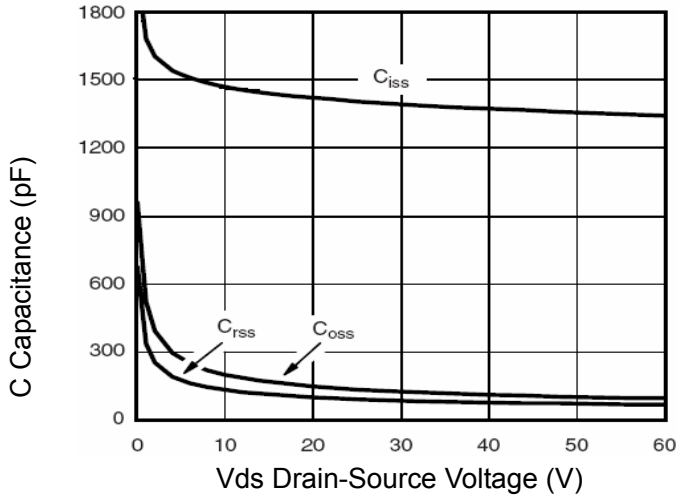


Figure 7 Capacitance vs Vds

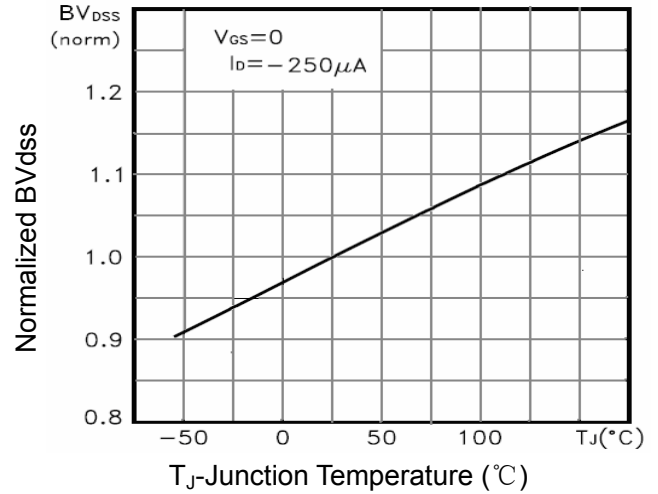


Figure 9 BV_{DSS} vs Junction Temperature

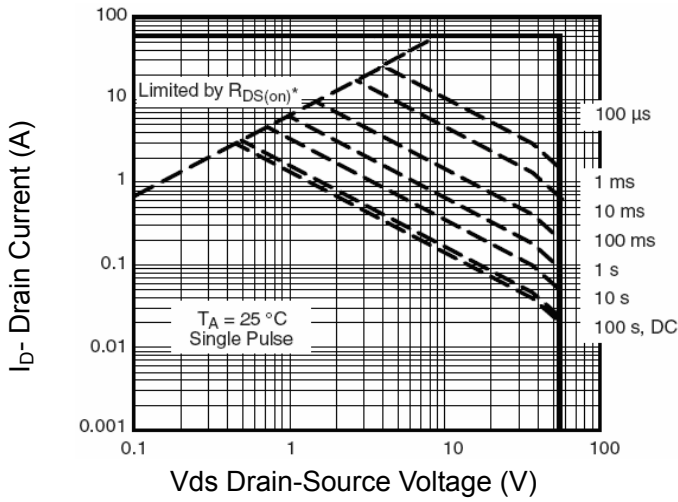


Figure 8 Safe Operation Area

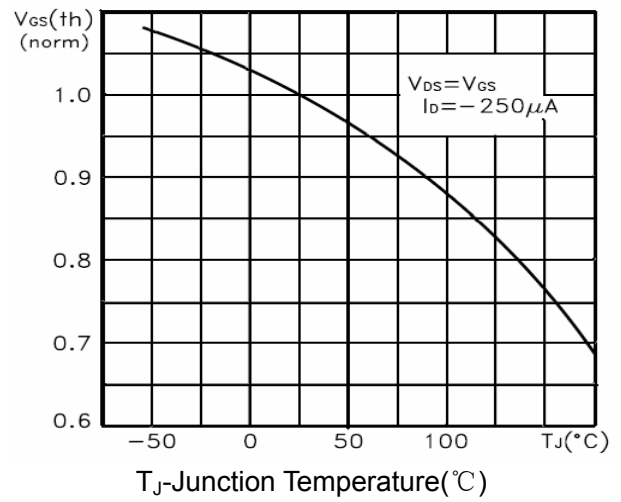


Figure 10 $V_{GS(th)}$ vs Junction Temperature

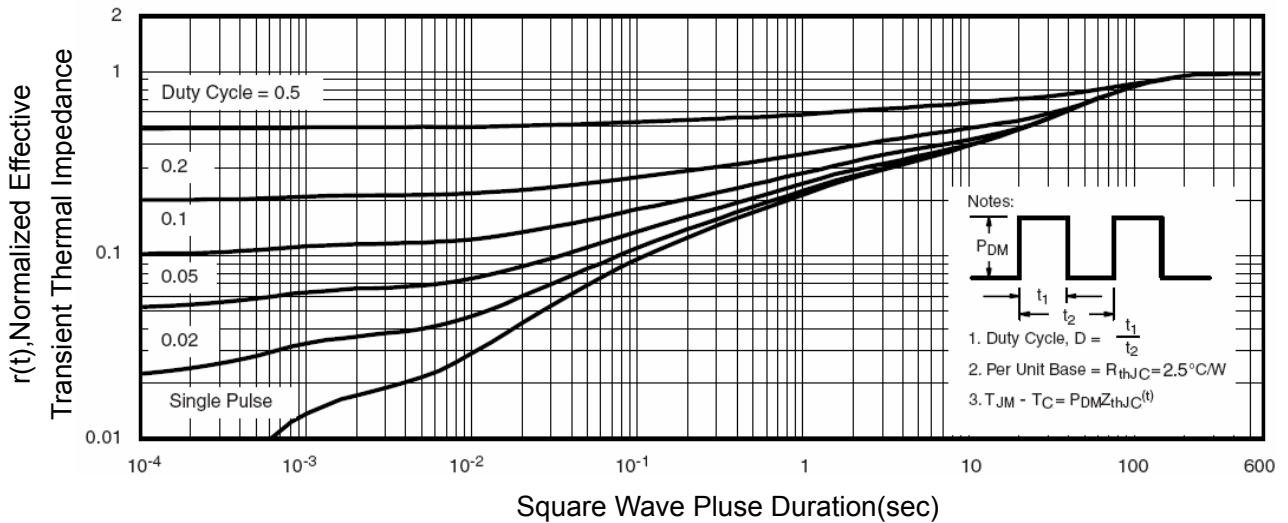


Figure 11 Normalized Maximum Transient Thermal Impedance